



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED  
DEC-3  
TECHNICAL UNIT  
#151C  
NOV 28 2001

In re the Application of: **Toshikazu INOUE et al.**

Serial Number: **09/473,988**

Group Art Unit: **2814**

Filed: **December 29, 1999**

Examiner: **T. Doan**

For: **SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME**

**AMENDMENT UNDER 37 CFR §1.111**

Commissioner for Patents  
Washington, D.C. 20231  
Sir:

November 28, 2001

In response to the Office Action dated August 28, 2001, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend claims 1, 2 and 7-9 as follows:

*See DI*  
1. (Three Times Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film and including a first insulating layer of a composition containing SiH, and a second insulating layer formed on said first insulating layer,

*C1*  
wherein said first insulating layer has an H content of not less than 15.4 atom% in the composition, and has been formed to cover said conductive film with a third insulating layer being interposed therebetween, and

said second insulating layer has a multilayer structure made up from layers of the same material.